Infrared Emitter (850 nm) Version 1.5

SFH 4850 E7800



Features:

- Wavelength 850nm
- · Anode is electrically connected to the case
- · Short switching times
- · Spectral match with silicon photodetectors
- · Measured with a 1.1mm aperture.
- DIN humidity caregory in acc. with DIN 40 040 GQG

Applications

- Photointerrupters
- Sensor technology
- · Light curtains

Notes

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Ordering Information

Туре:	Radiant Intensity	Ordering Code	
I _e [mW/sr]			
	I _F = 100 mA, t _p = 20 ms		
SFH 4850 E7800	10 (≥ 4)	Q65110A2093	

Note: measured at a solid angle of $\Omega = 0.01$ sr



$\underline{\text{Maximum Ratings } (T_C = 25 \, ^{\circ}\text{C})}$

Parameter	Symbol	Values	Unit
Operation and storage temperature range	T _{op} ; T _{stg}	-40 80	°C
Reverse voltage	V _R	5	V
Forward current	I _F	200	mA
Surge current $(t_p \le 1000 \ \mu s, D = 0)$	I _{FSM}	1	А
Power consumption	P _{tot}	470	mW
Thermal resistance junction - ambient	R _{thJA}	450	K/W
Thermal resistance junction - case	R _{thJC}	160	K/W
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V _{ESD}	2	kV

Characteristics $(T_A = 25 \, ^{\circ}C)$

Parameter		Symbol	Values	Unit
Peak wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	λ_{peak}	860	nm
Centroid wavelength ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	$\lambda_{\text{centroid}}$	850	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	Δλ	30	nm
Half angle	(typ)	φ	± 23	0
Dimensions of active chip area	(typ)	LxW	0.3 x 0.3	mm x mm
Rise and fall time of I_e (10% and 90% of $I_{e max}$) ($I_F = 100$ mA, $R_L = 50$ Ω)	(typ)	t _r , t _f	12	ns
Forward voltage $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ (max))	V _F	1.5 (≤ 1.8)	V
Forward voltage $(I_F = 1 \text{ A}, t_p = 100 \mu\text{s})$	(typ (max))	V _F	2.4 (≤ 3)	V
Reverse current (V _R = 5 V)		I _R	not designed for reverse operation	μΑ
Total radiant flux (I _F =100 mA, t _p =20 ms)	(typ)	Фе	50	mW



Parameter		Symbol	Values	Unit
Temperature coefficient of I_e or Φ_e ($I_F = 100$ mA, $t_p = 20$ ms)	(typ)	TC _i	-0.5	% / K
Temperature coefficient of V_F ($I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$)	(typ)	TC _V	-0.7	mV / K
Temperature coefficient of wavelength $(I_F = 100 \text{ mA}, t_p = 20 \text{ ms})$	(typ)	TC _λ	0.3	nm / K

Grouping $(T_A = 25 \, ^{\circ}C)$

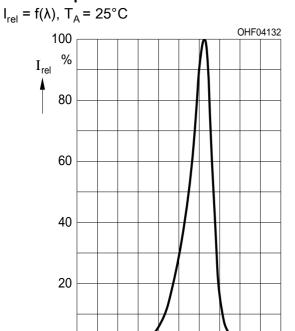
Group	Min Radiant Intensity	Max Radiant Intensity	Typ Radiant Intensity
	I _F = 100 mA, t _p = 20 ms	I _F = 100 mA, t _p = 20 ms	$I_F = 1 A, t_p = 100 \mu s$
	I _{e, min} [mW / sr]	I _{e, max} [mW / sr]	I _{e, typ} [mW / sr]
SFH 4850 E7800-P	4	8	50
SFH 4850 E7800-Q	6.3	12.5	75
SFH 4850 E7800-R	10	20	120

Note: Only one group in one packing unit (variation lower 2:1).

An aperture is used in front of the component for measurement of the radiant intensity and the half angle (diameter of the aperture: 1.1 mm; distance of aperture to case back side: 4.0 mm). This ensures that solely the radiation in axial direction emitting directly from the chip surface will be evaluated during measurement of the radiant intensity. Radiation reflected by the bottom plate (stray radiation) will not be evaluated. These reflections impair the projection of the chip surface by additional optics (e.g. long-range light reflection switches). In respect of the application of the component, these reflections are generally suppressed by apertures as well. This measuring procedure corresponding with the application provides more useful values. This aperture measurement is denoted by "E 7800" added to the type designation. Only one group in one packing unit (variation lower 2:1).



Relative Spectral Emission 1) page 9



Max. Permissible Forward Current

750

800

850

nm 950

λ

► T

0 <u></u>

$$I_{F, \text{ max}} = f(T_A), R_{\text{thJA}} = 450 \text{ K / W}$$

250

 I_F

mA

200

 $R_{\text{thJC}} = 160 \text{ K/W}$

150

 $R_{\text{thJA}} = 450 \text{ K/W}$

50

0

20

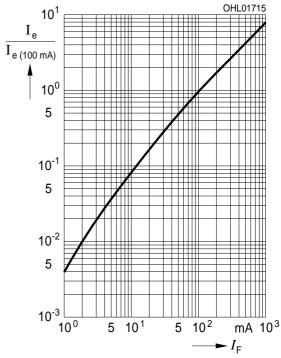
40

60

80 °C 100

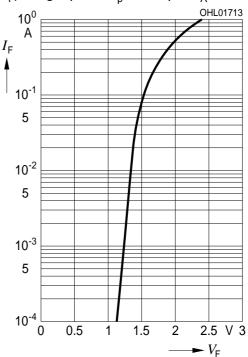
Radiant Intensity 1) page 9

 $I_{\rm e}$ / $I_{\rm e}$ (100 mA) = f($I_{\rm F}$), single pulse, $t_{\rm p}$ = 25 μ s, $T_{\rm A}$ = 25°C



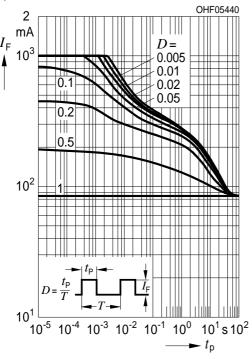
Forward Current 1) page 9

 $I_F = f(V_F)$, single pulse, $t_D = 100 \mu s$, $T_A = 25^{\circ} C$



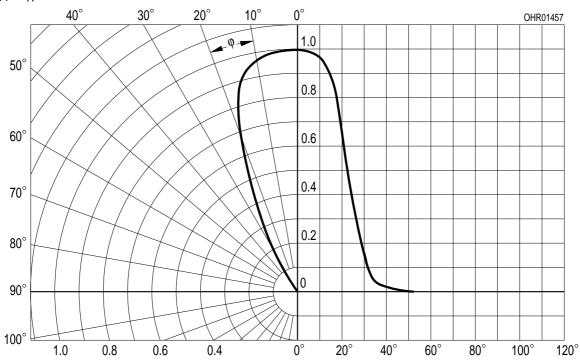
Permissible Pulse Handling Capability

 $I_F = f(t_p)$, $T_A = 25$ °C, duty cycle D = parameter

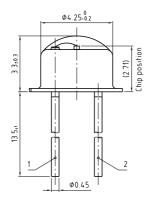


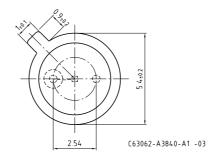
Radiation Characteristics 1) page 9

$$I_{rel} = f(\phi), T_A = 25^{\circ}C$$



Package Outline





Dimensions in mm.

Pinning

Pin	Description
1	Cathode
2	Anode

Package

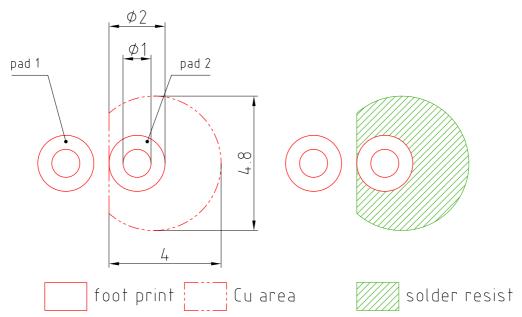
Metal Can (TO-18)

Approximate Weight:

0.2 g



Recommended Solder Pad



E062.3010.188-01

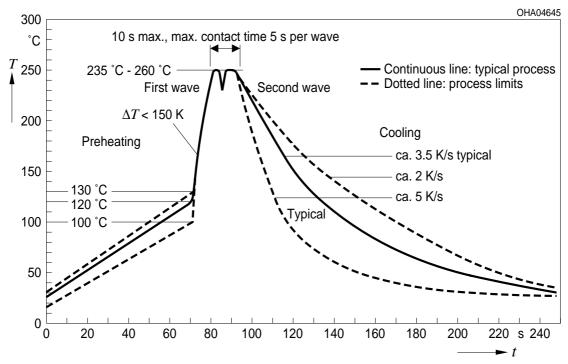
Dimensions in mm.

Note:

pad 1: cathode

TTW Soldering

IEC-61760-1 TTW





Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version in the Internet.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components* may only be used in life-support devices** or systems with the express written approval of OSRAM OS.

- *) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.
- **) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.



Glossary

Typical Values: Due to the special conditions of the manufacturing processes of LED, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.



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